



### 20V N-Channel Enhancement Mode MOSFET

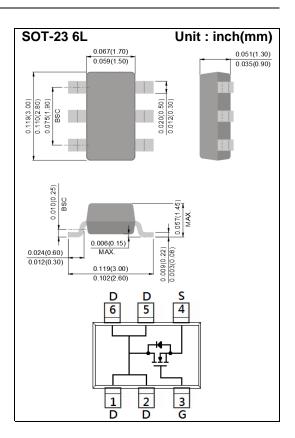
Voltage 20 V Current 7.4A

#### **Features**

- RDS(ON) , VGS@4.5V, ID@7.4A<27mΩ</li>
- RDS(ON), VGS@2.5V, ID@4.7A<41mΩ</li>
- RDS(ON), VGS@1.8V, ID@1.8A<85mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc..
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: S16



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 12	V
Continuous Drain Current		I <sub>D</sub>	7.4	Α
Pulsed Drain Current		I <sub>DM</sub>	29.6	Α
Power Dissipation	T <sub>a</sub> =25°C	· P <sub>D</sub>	2	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance				
- Junction to Ambient <sup>(Note 3)</sup>		$R_{ heta JA}$	62.5	°C/W





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.77	1.2	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =7.4A	-	24	27	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =4.7A	-	33	41	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.8A	-	62	85	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =7.4A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	6.8	-	nC
Gate-Source Charge	$Q_gs$		-	1.3	-	
Gate-Drain Charge	$Q_{gd}$		-	2	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	513	-	pF
Output Capacitance	Coss		-	74	-	
Reverse Transfer Capacitance	Crss		-	60	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	$\begin{array}{c} V_{DD}{=}10V,\ I_{D}{=}7.4A, \\ V_{GS}{=}4.5V, \\ R_{G}{=}6\Omega^{(Note\ 1,2)} \end{array}$	-	7	-	ns
Turn-On Rise Time	tr		-	57	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	24	-	
Turn-Off Fall Time	tf		-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	2.0	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.69	1.2	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### **TYPICAL CHARACTERISTIC CURVES**

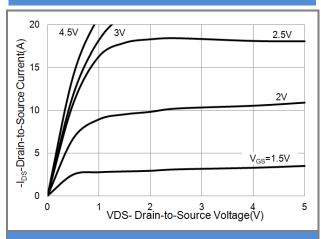


Fig.1 On-Region Characteristics

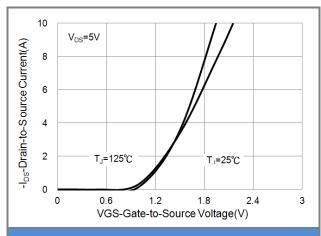


Fig.2 Transfer Characteristics

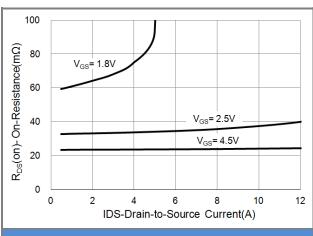


Fig.3 On-Resistance vs. Drain Current

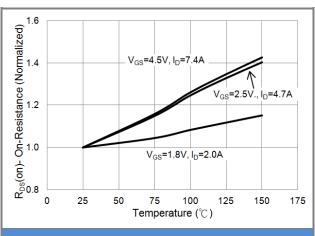
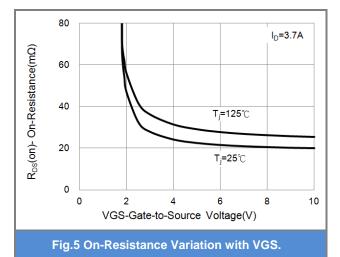
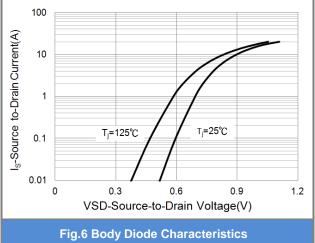


Fig.4 On-Resistance vs. Junction temperature

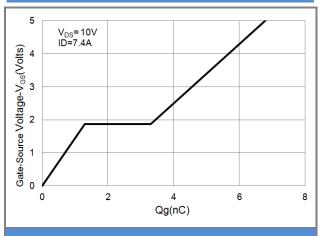








### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

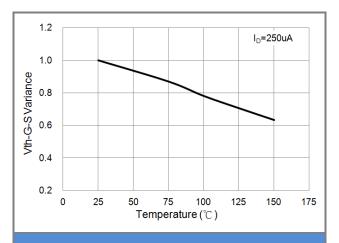


Fig.8 Threshold Voltage Variation with Temperature.

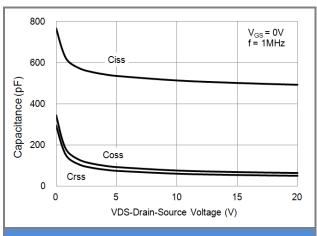


Fig.9 Capacitance vs. Drain-Source Voltage.

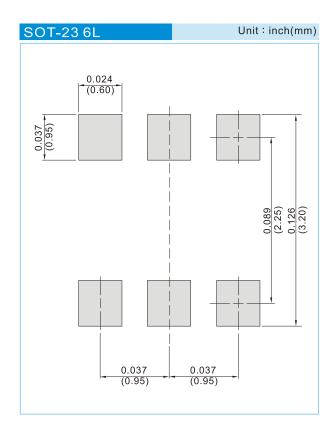




### PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6416_S1_00001	SOT-23 6L	3K pcs / 7" reel	S16	Halogen free RoHS compliant
PJS6416_S2_00001	SOT-23 6L	10K pcs / 13" reel	S16	Halogen free RoHS compliant

### **MOUNTING PAD LAYOUT**







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